

SN54HC4016, TLC4016I

SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

D2922, JANUARY 1986

- High Degree of Linearity
- High On-Off Output Voltage Ratio
- Low Crosstalk Between Switches
- Low On-State Impedance of 50 Ohms Typ at V_{CC} = 9 V
- Individual Switch Controls
- Extremely Low Input Current

description

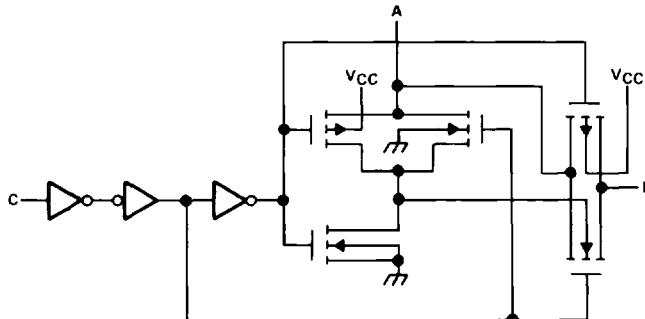
The TLC4016 is a silicon-gate CMOS quadruple analog switch integrated circuit designed to handle both analog and digital signals. Each switch permits signals with amplitudes up to 12 volts peak to be transmitted in either direction.

Each switch section has its own enable input control. A high-level voltage applied to this control terminal turns on the associated switch section.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

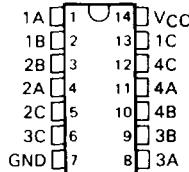
The SN54HC4016 is characterized for operation from -55°C to 125°C, and the TLC4016I is characterized from -40°C to 85°C.

logic diagram (positive logic)

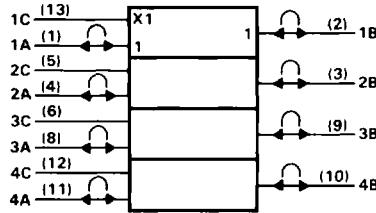


**SN54HC4016 . . . J OR N PACKAGE
TLC4016I . . . D OR N PACKAGE**

(TOP VIEW)



logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91 1984 and IEC Publication 617 12.

2

HCMOS Devices

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

Copyright © 1986, Texas Instruments Incorporated

**TEXAS
INSTRUMENTS**

POST OFFICE BOX 655012 • DALLAS, TEXAS 75265

2-617

**SN54HC4016, TLC4016I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH**

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

NOTES: 1. All voltages are with respect to ground unless otherwise specified.
2. For operation above 25°C free-air temperature, see Dissipation Derating Table.

DISSIPATION DERATING TABLE

Package	Maximum Power Dissipation			Derating Factor
	25°C	85°C	125°C	
D	950 mW	494 mW		7.6 mW/°C
J	1025 mW	533 mW	205 mW	8.2 mW/°C
N	875 mW	455 mW	175 mW	7.0 mW/°C

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}		2 ¹	5	12	V
I/O port voltage, $V_{I/O}$		0		V_{CC}	V
High level input voltage, V_{IH}	$V_{CC} = 2\text{ V}$	1.5		V_{CC}	V
	$V_{CC} = 4.5\text{ V}$	3.15		V_{CC}	
	$V_{CC} = 9\text{ V}$	6.3		V_{CC}	
	$V_{CC} = 12\text{ V}$	8.4		V_{CC}	
Low-level input voltage, V_{IL}	$V_{CC} = 2\text{ V}$	0	0.3		V
	$V_{CC} = 4.5\text{ V}$	0	0.9		
	$V_{CC} = 9\text{ V}$	0	1.8		
	$V_{CC} = 12\text{ V}$	0	2.4		
Input rise time, t_r	$V_{CC} = 2\text{ V}$		1000		ns
	$V_{CC} = 4.5\text{ V}$		500		
	$V_{CC} = 9\text{ V}$		400		
Input fall time, t_f	$V_{CC} = 2\text{ V}$		1000		ns
	$V_{CC} = 4.5\text{ V}$		500		
	$V_{CC} = 9\text{ V}$		400		
Operating free-air temperature, T_A	SN54HC4016	55	125		$^{\circ}\text{C}$
	TLC4016I	40	85		

[†]With supply voltages at or near 2 volts, the analog switch on-state resistance becomes very nonlinear. It is recommended that only digital signals be transmitted at these low supply voltages.

SN54HC4016, TLC4016I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

2

HCMOS Devices

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V_{CC}	SN54HC4016			TLC4016I			UNIT
				MIN	TYP[†]	MAX	MIN	TYP[†]	MAX	
<i>I_{Son}</i> On state switch resistance	<i>I_S</i> = 1 mA, <i>V_A</i> = 0 to <i>V_{CC}</i> . See Figure 1	4.5 V		100	220		100	200		Ω
		9 V		50	120		50	105		
		12 V		30	100		30	85		
		2 V		120	240		120	215		
	<i>I_S</i> = 1 mA, <i>V_A</i> = 0 or <i>V_{CC}</i> . See Figure 1	4.5 V		50	120		50	100		
		9 V		35	80		35	75		
		12 V		20	70		20	60		
		4.5 V		10	20		10	20		
<i>I_I</i> Control input current	<i>V_I</i> = 0 or <i>V_{CC}</i> . See Figure 1	9 V		5	15		5	15		μA
		12 V		5	15		5	15		
		2 V		+1		-1				
<i>I_{loff}</i> Off state switch leakage current	<i>V_S</i> = <i>V_{CC}</i> . See Figure 2	to TA = 25°C		-0.1		+0.1				nA
		5.5 V		-10	+600		-10	+600		
		9 V		-15	+800		-15	+800		
<i>I_{Soff}</i> On state switch leakage current	<i>V_A</i> = 0 or <i>V_{CC}</i> . See Figure 3	12 V		-20	+1000		-20	+1000		nA
		5.5 V		-10	+150		-10	+150		
		9 V		-15	+200		-15	+200		
<i>I_{CC}</i> Supply current	<i>V_I</i> = 0 or <i>V_{CC}</i> . <i>I_O</i> = 0	12 V		-20	+300		-20	+300		μA
		5.5 V		2	40		2	20		
		9 V		8	160		8	80		
<i>C_i</i> Input capacitance	A or B		12 V	16	320		16	160		pF
		2 V to		15		15				
	C	12 V		5	10		5	10		
<i>C_f</i> Feedthrough capacitance	A to B	<i>V_I</i> = 0	2 V to 12 V		5		5			pF

[†]All typical values are at TA = 25°C.



POST OFFICE BOX 655012 • DALLAS, TEXAS 75265

SN54HC4016, TLC4016I SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

switching characteristics over recommended operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	SN54HC4016			TLC4016I			UNIT
			MIN	TYP [†]	MAX	MIN	TYP [†]	MAX	
t_{pd} Propagation delay time, A to B or B to A	See Figure 4	2 V	25	75		25	62		ns
		4.5 V	5	15		5	13		
		9 V	4	14		4	12		
		12 V	3	13		3	11		
t_{on} Switch turn-on time	$R_L = 1 \text{ k}\Omega$, See Figures 5 and 6	2 V	32	150		32	125		ns
		4.5 V	8	30		8	25		
		9 V	6	18		6	15		
		12 V	5	15		5	13		
t_{off} Switch turn-off time	$R_L = 1 \text{ k}\Omega$, See Figures 5 and 6	2 V	45	252		45	210		ns
		4.5 V	15	54		15	45		
		9 V	10	48		10	40		
		12 V	8	45		8*	38		
f_{co} Switch cutoff frequency (channel loss = 3 dB)		4.5 V	100			100			MHz
		9 V	120			120			
V _{OCF(PP)} Control feedthrough voltage to any switch, peak to peak	See Figure 7	4.5 V	180			180			mV
Frequency at which crosstalk attenuation between any two switches equals 50 dB	See Figure 8	4.5 V	1			1			MHz

[†]All typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER MEASUREMENT INFORMATION

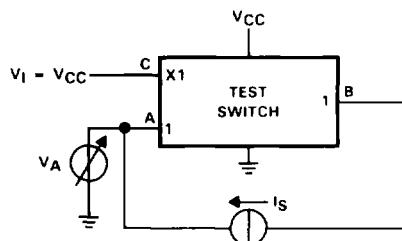
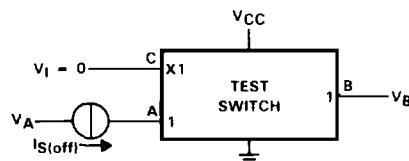


FIGURE 1. ON-STATE RESISTANCE TEST CIRCUIT



$V_S = V_A - V_B$
CONDITION 1: $V_A = 0$, $V_B = V_{CC}$
CONDITION 2: $V_A = V_{CC}$, $V_B = 0$

FIGURE 2. OFF-STATE SWITCH LEAKAGE CURRENT TEST CIRCUIT

PARAMETER MEASUREMENT INFORMATION

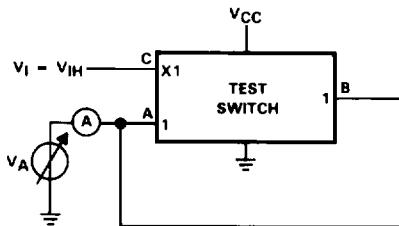


FIGURE 3. ON-STATE SWITCH LEAKAGE CURRENT TEST CIRCUIT

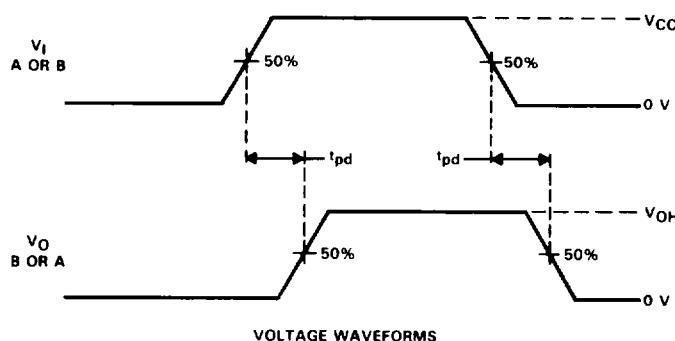
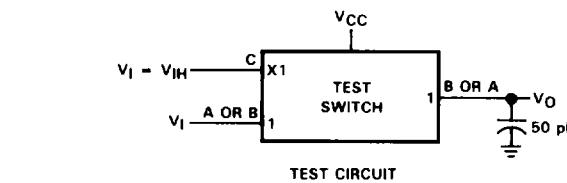


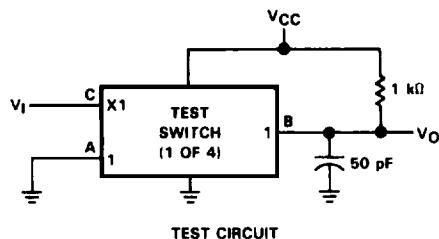
FIGURE 4. PROPAGATION DELAY TIME, SIGNAL INPUT TO SIGNAL OUTPUT

SN54HC4016, TLC4016I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

2

HCMOS Devices

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

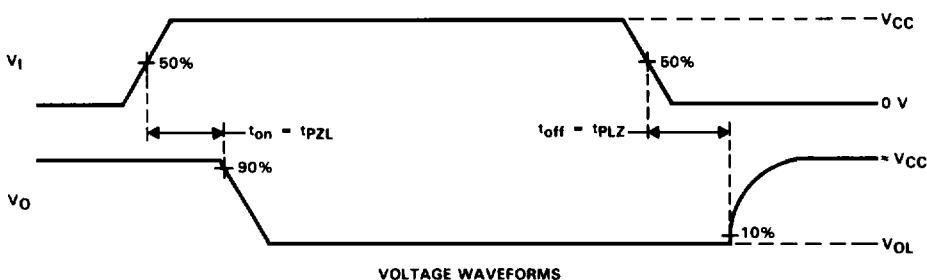


FIGURE 5. SWITCHING TIME (t_{PZL} , t_{PLZ}), CONTROL TO SIGNAL OUTPUT

PARAMETER MEASUREMENT INFORMATION

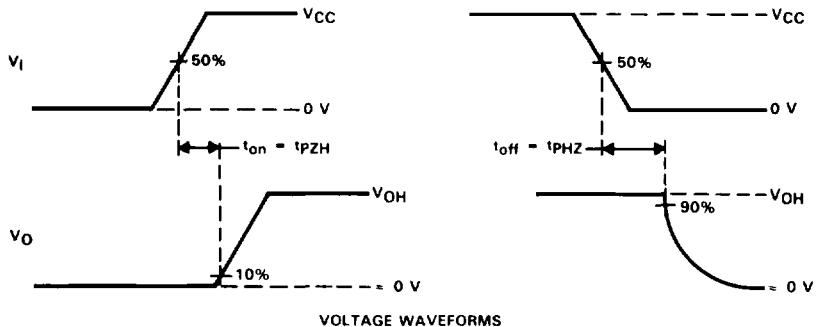
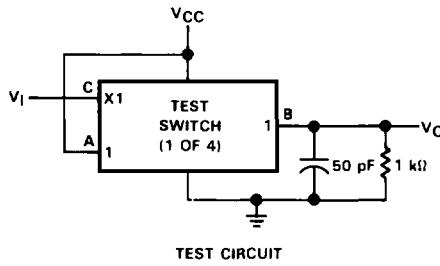


FIGURE 6. SWITCHING TIME (t_{PZH} , t_{PHZ}). CONTROL TO SIGNAL OUTPUT

TEXAS
 INSTRUMENTS

POST OFFICE BOX 655012 • DALLAS, TEXAS 75285

2-623

**SN54HC4016, TLC4016I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH**

2

HCMOS Devices

PARAMETER MEASUREMENT INFORMATION

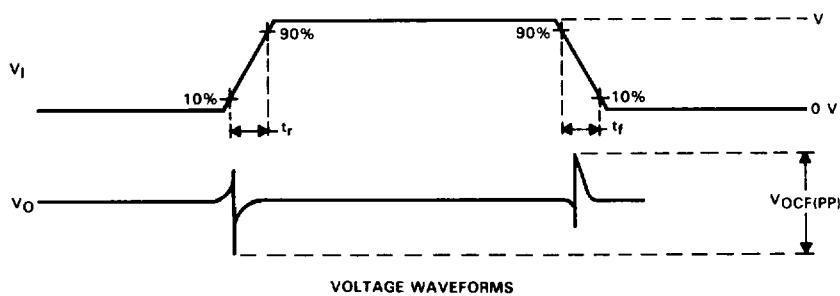
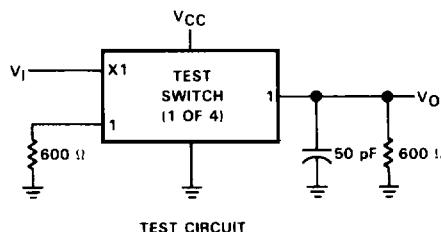


FIGURE 7. CONTROL FEEDTHROUGH VOLTAGE

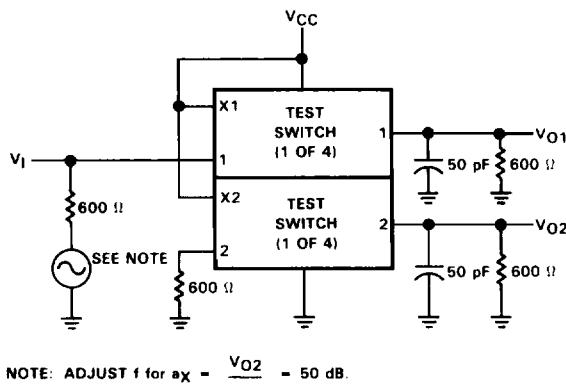


FIGURE 8. CROSSTALK BETWEEN ANY TWO SWITCHES, TEST CIRCUIT